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EUROPEAN PATENT APPLICATION

21 Application number: 87308050.1

51 Int. Cl.4: **H 01 L 23/48**
H 01 L 23/52

22 Date of filing: 11.09.87

30 Priority: 17.09.86 JP 218302/86

43 Date of publication of application:
 01.06.88 Bulletin 88/22

84 Designated Contracting States: DE FR GB

88 Date of deferred publication of search report:
 17.08.88 Bulletin 88/33

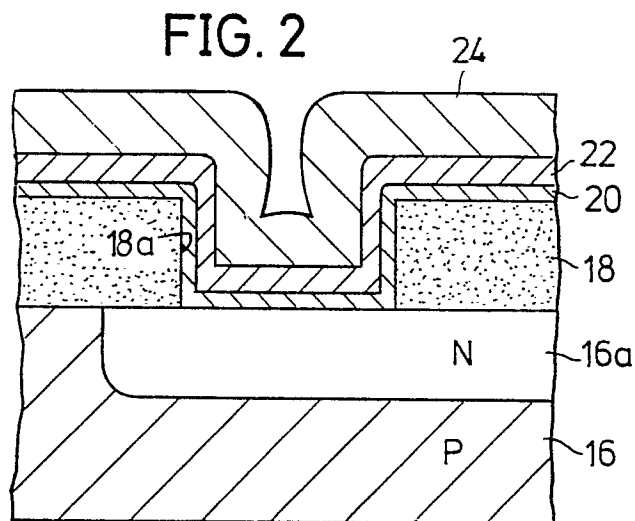
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54 Semiconductor device having a metallic layer.

57 A semiconductor device comprises a silicon substrate (16), an insulating film (18) in which a contact hole (18a) is formed, a metallic layer (20) deposited on said silicon substrate through the contact hole, for forming an ohmic contact to the silicon substrate, a diffusion barrier layer (22) deposited on the metallic layer, for preventing reaction and interdiffusion between copper and silicon, and a metallization film (24) including at least copper deposited on the barrier layer.





European Patent
Office

EUROPEAN SEARCH REPORT

Application Number

EP 87 30 8050

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. Cl.4)
Y	PATENT ABSTRACTS OF JAPAN, vol. 9, no. 75 (E-306)[1798], 4th April 1985; & JP-A-59 210 656 (FUJITSU K.K.) 29-11-1984 * Abstract *	1-7	H 01 L 23/48 H 01 L 23/52
Y	IBM TECHNICAL DISCLOSURE BULLETIN, vol. 29, no. 3, August 1986, pages 1395,1396, New York, US; "Diffusion barriers for CU" * The whole article *	1-7	
A	IBM TECHNICAL DISCLOSURE BULLETIN, vol. 25, no. 2, July 1982, pages 591-592, New York, US; R.C.LANGE et al.: "Process for forming a contact hole stud"	1-4	
E	EP-A-0 261 846 (FUJITSU) * Figures; page 3, lines 14-39 *	1-7	
			TECHNICAL FIELDS SEARCHED (Int. Cl.4)
			H 01 L
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 03-05-1988	Examiner CAMPLING N.C.G.
CATEGORY OF CITED DOCUMENTS X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document			